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Parrainage ou lien avec des sociétés savantes, des GDR ou autres structures : Les **JSI, Journées Surfaces interfaces** identifient bien la communauté concernée. **Chaque année**, ces journées regroupent **une centaine d'experts** dans les domaines de la physique et de la chimie des surfaces et des interfaces. Les thématiques abordées concernent aussi bien la structure, la morphologie, et la réactivité des surfaces et des interfaces que leurs propriétés électroniques, magnétiques ou optiques. De par l'importance des surfaces et des interfaces dans les nanostructures, les nanosciences trouvent naturellement une place de choix dans ce mini-colloque.

Résumé

The purpose of this mini-colloquium is to review topics where properties and/or functionalities are built at the interface of materials and to identify when the atomic level control/knowledge is relevant for applications.

The role of intermixing and concentration profile in interfaces will be addressed. For this purpose photoelectrons spectroscopies such as XPS, HAXPES and standing wave are most relevant.

The structural quality of the interfaces take a specific place when dealing with epitaxial growth as well as nanomaterials.

Electronic properties at the interfaces starting with band alignment, build-in electric field and charge transfer will be also addressed in the case of oxide and/or semiconductor based interfaces

Although the scope seems very large it is relevant to share methods and knowhow between research on different topics.

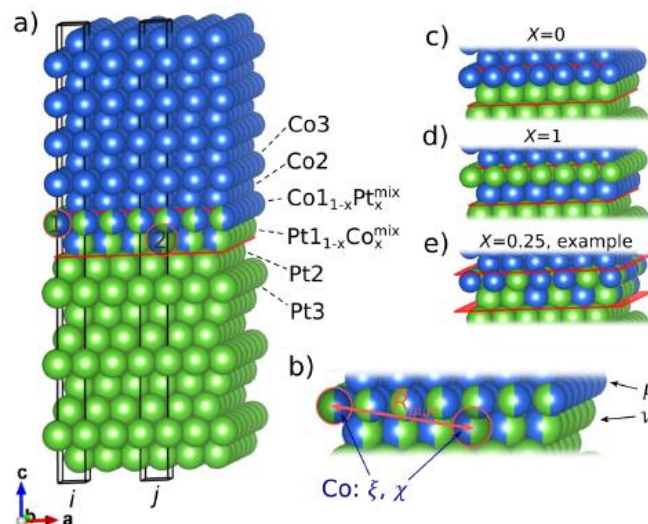


Figure Schematic drawing of the Co/Pt bilayer. Red planes highlight the interface region where intermixing is introduced (from Ref 1-)

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